

*IN THE SPECIFICATION:*

*Replace the paragraph beginning at page 1, line 13, with:*

A1

Main circuit 610 includes an input terminal 6101, a transistor 6102, transmission lines 6103 and 6104, and an output terminal 6105. Transistor 6102 is connected to input terminal 6101 at its gate terminal, to a ground node 7 at its source terminal, and to transmission line 6103 at its drain terminal. Transistor 6102 is, to be specific, a field effect transistor such as a MOS FET, or a MES FET (Metal Semiconductor Field Effect Transistor), HEMT (High Electron Mobility Transistor) or HBT (Heterojunction Bipolar Transistor) made from GaAs.

*Replace the paragraph beginning at page 2, line 18, with:*

A2

In prior art high frequency semiconductor integrated circuit 600, however, circuit block 620 is connected to node 6106 of main circuit 610; therefore, when only main circuit 610 is desired to be used, or when a high frequency semiconductor integrated circuit having a different performance is requested, a problem arises since separate circuit patterns are required. That is, when passive circuits 6201 and 6202, each constituted of a passive element optimized for output matching, are incorporated into circuit block 620, only main circuit 610 cannot be used and further, high frequency semiconductor integrated circuit 600 cannot be differently used as a high frequency semiconductor integrated circuit for achieving efficiency matching.

*Replace the paragraph beginning at page 6, line 22, with:*

A3

Fig. 21 is a plan view showing a specific example of one of two high frequency semiconductor integrated circuits shown in Fig. 20; and